

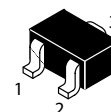
## Surface Mount Switching Diode

\* “G” Lead(Pb)-Free

### Features:

- \*Low Current Leakage
- \*Low Forward Voltage
- \*Reverse Recover Time  $T_{rr} \leq 6\text{ns}$
- \*Small Outline Surface Mount SOT-323 Package

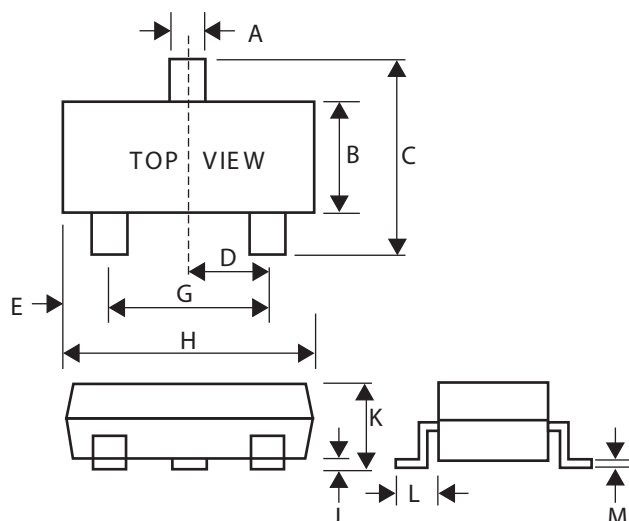
**SWITCHING DIODE  
200-215m AMPERRES  
70-75 VOLTS**



**SOT-323(SC-70)**

## SOT-323 Outline Demensions

Unit:mm



**SOT-323**

Dim	Min	Max
<b>A</b>	0.30	0.40
<b>B</b>	1.15	1.35
<b>C</b>	2.00	2.40
<b>D</b>	-	0.65
<b>E</b>	0.30	0.40
<b>G</b>	1.20	1.40
<b>H</b>	1.80	2.20
<b>J</b>	0.00	0.10
<b>K</b>	0.80	1.00
<b>L</b>	0.42	0.53
<b>M</b>	0.10	0.25

### Maximum Ratings (EACH DIODE)

Characteristic	Symbol	BAS16W	BAV70W	BAW56W	BAV99W	Unit
Reverse Voltage	V <sub>R</sub>	75	70			Volts
Forward Current	I <sub>F</sub>	200			215	mAdc
Peak Forward Surge Current	I <sub>FM</sub>	500				mAdc

### Thermal Characteristics

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board *1, TA=25°C Derate Above 25°C	P <sub>D</sub>	200 1.6	mW mW/°C
Thermal Resistance Junction to Ambient	R <sub>θJA</sub>	625	°C/W
Total Device Dissipation Alumina Substrate *2 TA=25°C Derate Above 25°C	P <sub>D</sub>	300 2.4	mW mW/°C
Thermal Resistance Junction to Ambient	R <sub>θJA</sub>	417	°C/W
Junction and Storage Temperature	T <sub>J</sub> , T <sub>stg</sub>	-55 to + 150	°C

\*1 ER-5=1.0x0.75x0.062 in

\*2 Alumina=0.4x0.3x0.024 in 99.5% Alumina

### Electrical Characteristics (TA=25°C Unless Otherwise Note) (Each Diode)

Characteristic	Symbol	Min	Max	Unit
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### Off Characteristics

Reverse Breakdown Voltage BAS16W (I <sub>BR</sub> =100μAdc ) BAV70W/BAW56W/BAV99W	V <sub>BR</sub>	75 70		Vdc
Reverse Voltage Leakage Current V <sub>R</sub> =75V BAS16W V <sub>R</sub> =70V BAV70W/BAW56W/BAV99W			1.0 2.5	
V <sub>R</sub> =25V, T <sub>J</sub> =150°C BAS16W/BAW56W/BAV99W V <sub>R</sub> =25V, T <sub>J</sub> =150°C BAV70W	I <sub>R</sub>		30.0 60.0	μAdc
V <sub>R</sub> =75V, T <sub>J</sub> =150°C BAS16W V <sub>R</sub> =70V, T <sub>J</sub> =150°C BAW56W/BAV99W V <sub>R</sub> =70V, T <sub>J</sub> =150°C BAV70W			50.0 50.0 100.0	

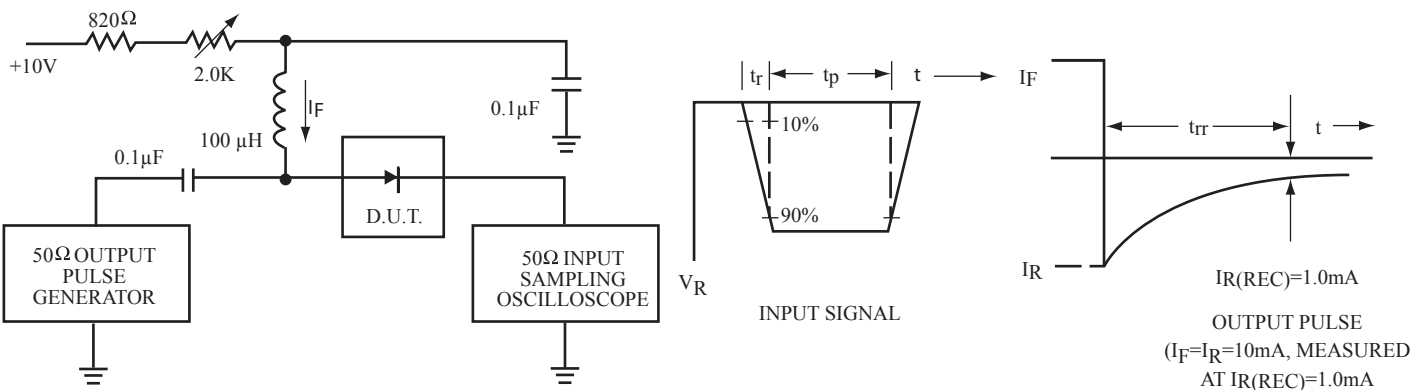
**Off Characteristic**

Characteristic	Symbol	Min	Max	Unit
Diode Capacitance (V <sub>R</sub> =0, f=1.0MHz) BAS16W/BAW56W BAV70W/BAV99W	C <sub>D</sub>		2.0 1.5	PF
Forward Voltage (I <sub>F</sub> =1.0 mA) (I <sub>F</sub> =10 mA) (I <sub>F</sub> =50 mA) (I <sub>F</sub> =150 mA)	V <sub>F</sub>		715 855 1000 1250	mVdc
Reverse Recovery Time (Figure 1.) I <sub>F</sub> =I <sub>R</sub> =10 mA, V <sub>R</sub> =5.0Vdc I <sub>R</sub> (REC)=1.0 mA, R <sub>L</sub> =100Ω	t <sub>rr</sub>		6.0	nS

**Device Marking**

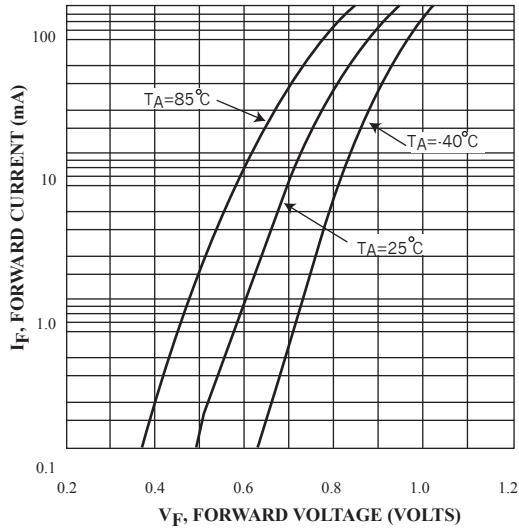
Item	Marking	Equivalent Circuit diagram
BAS16W	A6	
BAV70W	A4	
BAW56W	A1	
BAV99W	A7	

**Figure 1. Recovery Time Equivalent Test Circuit**

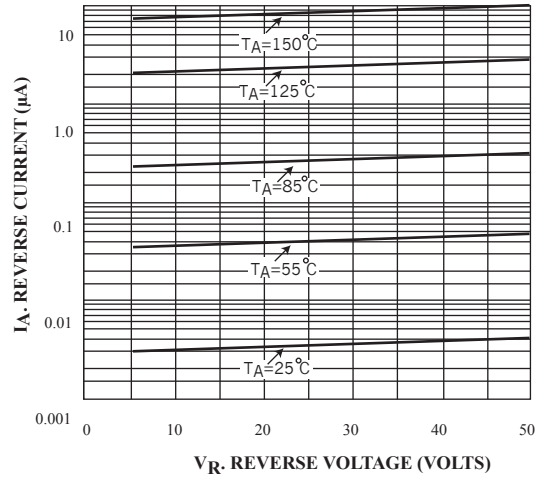


- Notes: 1. A 2.0 kΩ variable resistor for a Forward Current (I<sub>F</sub>) of 10 mA
- 2. Input pulses is adjusted so I<sub>R</sub>(peak) is equal to 10 mA
- 3. t<sub>p</sub> >> t<sub>rr</sub>

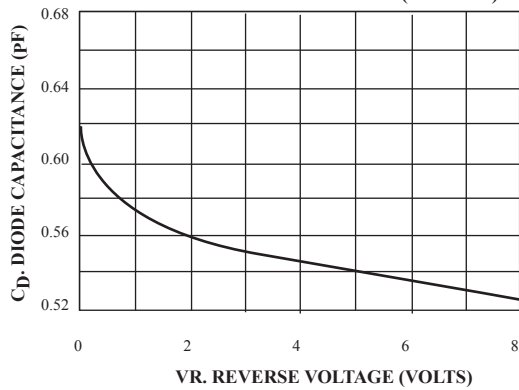
**FIGURE 2 .FORWARD VOLTAGE**



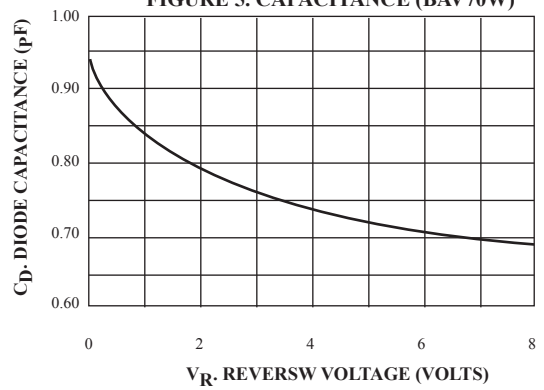
**FIGURE 3. LEAKAGE CURRENT**



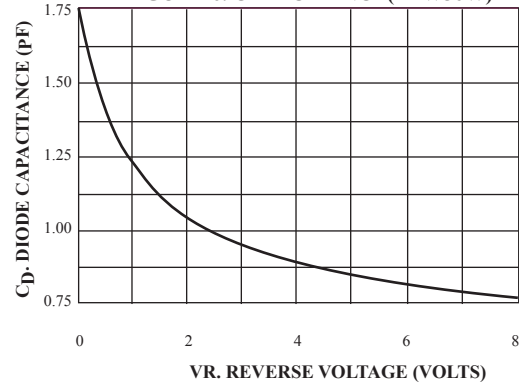
**FIGURE 4. CAPACITANCE(BAS16W)**



**FIGURE 5. CAPACITANCE (BAV70W)**



**FIGURE 6. CAPACITANCE(BAW56W)**



**FIGURE 7. CAPACITANCE (BAV99W)**

